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Patents

PAT. NO.	Title
7,718,130	Integrated thin-film sensors and methods (2010) Co-Inventors: R. Shinar, J. Shinar
4,692,558	Counteraction of semiconductor impurity effects :
4,604,636	Microcrystalline semiconductor method and devices :
4,485,128	Bandgap control in amorphous semiconductors :
4,478,654	Amorphous silicon carbide method (co-inventor, S. Gau)
4,477,688	Photovoltaic cells employing zinc phosphide : (Co-inventor)
4,465,706	Bandgap control in amorphous semiconductors :
4,387,265	Tandem junction amorphous semiconductor photovoltaic cell :
4,377,723	High efficiency thin-film multiple-gap photovoltaic device :
4,253,882	Multiple gap photovoltaic device
4,251,287	Amorphous semiconductor solar cell :
3,988,167	Solar cell device having improved efficiency : Co-Inventor: H. Kressel